Denis Flandre

List of Publications by Year
in descending order

664 papers	9,635 citations	57719 44 h-index	88593 70 g-index
671 all docs	671 docs citations	671 times ranked	5257 citing authors

#	Article	IF	Citations
1	Analysis and Design of RF Energy-Harvesting Systems With Impedance-Aware Rectifier Sizing. IEEE Transactions on Circuits and Systems II: Express Briefs, 2023, 70, 361-365.	2.2	4
2	Characterization of thin Al2O3/SiO2 dielectric stack for CMOS transistors. Microelectronic Engineering, 2022, 254, 111708.	1.1	10
3	An Ultra-Thin Ultraviolet Enhanced Backside-Illuminated Single-Photon Avalanche Diode With 650 nm-Thin Silicon Body Based on SOI Technology. IEEE Journal of Selected Topics in Quantum Electronics, 2022, 28, 1-10.	1.9	2
4	Comprehensive Analytical Comparison of Ring Oscillators in FDSOI Technology: Current Starving Versus Back-Bias Control. IEEE Transactions on Circuits and Systems I: Regular Papers, 2022, 69, 1883-1895.	3.5	6
5	An Ultra-Low-Power Read-Out Circuit for Interfacing Novel Gas Sensors Matrices. IEEE Sensors Journal, 2022, 22, 9521-9533.	2.4	7
6	Accurate and Insightful Closed-Form Prediction of Subthreshold SRAM Hold Failure Rate. IEEE Transactions on Circuits and Systems I: Regular Papers, 2022, 69, 2767-2780.	3.5	1
7	Design-Window Methodology for Inductorless Noise-Cancelling CMOS LNAs. IEEE Access, 2022, 10, 29482-29492.	2.6	3
8	Spike-Based Sensing and Communication for Highly Energy-Efficient Sensor Edge Nodes. , 2022, , .		4
9	High-performance dual-mode ultra-thin broadband CdS/CIGS heterojunction photodetector on steel. Optics Express, 2022, 30, 13875.	1.7	11
10	Characteristics of noise degradation and recovery in gamma-irradiated SOI nMOSFET with in-situ thermal annealing. Solid-State Electronics, 2022, , 108300.	0.8	0
11	Low-power silicon strain sensor based on CMOS current reference topology. Sensors and Actuators A: Physical, 2022, 339, 113491.	2.0	0
12	SiO_x Patterned Based Substrates Implemented in Cu(In,Ga)Se₂ Ultrathin Solar Cells: Optimum Thickness. IEEE Journal of Photovoltaics, 2022, 12, 954-961.	1.5	4
13	Investigation and optimization of traps properties in Al2O3/SiO2 dielectric stacks using conductance method. Solid-State Electronics, 2022, 194, 108347.	0.8	2
14	Experimental study of thermal coupling effects in FD-SOI MOSFET. Solid-State Electronics, 2022, 194, 108362.	0.8	1
15	Correlation and optimization of the optoelectrical properties of DC magnetron-sputtered Cu2ZnSnS4 absorber layer as a function of the material composition. Materials Science in Semiconductor Processing, 2021, 121, 105367.	1.9	4
16	Extensive Electrical Characterization Methodology of Advanced MOSFETs Towards Analog and RF Applications. IEEE Journal of the Electron Devices Society, 2021, 9, 500-510.	1.2	9
17	A Physical Model of Contact Resistance in Ti-Contacted Graphene-Based Field Effect Transistors. IEEE Transactions on Electron Devices, 2021, 68, 892-898.	1.6	4
18	15.3: Defect Engineering in nâ€Type Oxide Semiconductor TFTs. Digest of Technical Papers SID International Symposium, 2021, 52, 101-101.	0.1	0

#	Article	IF	Citations
19	A Wearable Low-Power Sensing Platform for Environmental and Health Monitoring: The Convergence Project. Sensors, 2021, 21, 1802.	2.1	12
20	Determination of Carrier Lifetime in Silicon Using an Ultra-thin Al₂O₃/SiO₂ Dielectric Stack. , 2021, , .		1
21	Depletion effects in moderately doped TiO2 layers from Câ€“V characteristics of MIS structures on Si. Applied Physics Express, 2021, 14, 051008.	1.1	1
22	Improved Split CV Mobility Extraction in 28 nm Fully Depleted Silicon on Insulator Transistors. IEEE Electron Device Letters, 2021, 42, 661-664.	2.2	2
23	High-responsivity broadband photodetection of an ultra-thin In₂S₃/CIGS heterojunction on steel. Optics Letters, 2021, 46, 2288.	1.7	7
24	Comparative Study of Al₂O₃ and HfO₂ for Surface Passivation of Cu(In,Ga)Se₂ Thin Films: An Innovative Al₂O₃/HfO₂ Multistack Design. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2100073.	0.8	5
25	The shift of breakdown voltage for silicon membrane strip detectors resulting from surface avalanche. Journal of Applied Physics, 2021, 129, 214501.	1.1	0
26	A Self-Gating RF Energy Harvester for Wireless Power Transfer With High-PAPR Incident Waveform. IEEE Journal of Solid-State Circuits, 2021, 56, 1816-1826.	3.5	11
27	SleepRunner: A 28-nm FDSOI ULP Cortex-M0 MCU With ULL SRAM and UFBR PVT Compensation for 2.6â€“3.6-Î¼W/DMIPS 40â€“80-MHz Active Mode and 131-nW/kB Fully Retentive Deep-Sleep Mode. IEEE Journal of Solid-State Circuits, 2021, 56, 2256-2269.	3.5	18
28	Trap Recovery by in-Situ Annealing in Fully-Depleted MOSFET With Active Silicide Resistor. IEEE Electron Device Letters, 2021, 42, 1085-1088.	2.2	6
29	Origin of low-temperature negative transconductance in multilayer MoS2 transistors. Applied Physics Letters, 2021, 119, .	1.5	1
30	Indirect light absorption model for highly strained silicon infrared sensors. Journal of Applied Physics, 2021, 130, .	1.1	6
31	29.3: Invited Paper: Defect Engineering in n â€Type Oxide Semiconductor TFTs. Digest of Technical Papers SID International Symposium, 2021, 52, 400-400.	0.1	0
32	Perovskite Metalâ€“Oxideâ€“Semiconductor Structures for Interface Characterization. Advanced Materials Interfaces, 2021, 8, 2101004.	1.9	1
33	Temperature-dependent performance of Schottky-Barrier FET ultra-low-power diode. Solid-State Electronics, 2021, 184, 108124.	0.8	0
34	Highâ€Performance and Industrially Viable Nanostructured SiO_x Layers for Interface Passivation in Thin Film Solar Cells. Solar Rrl, 2021, 5, 2000534.	3.1	15
35	The Impact of LCE and PAMDLE Regarding Different CMOS ICs Nodes and High Temperatures. IEEE Journal of the Electron Devices Society, 2021, 9, 415-423.	1.2	5
36	Non-Linear Output-Conductance Function for Robust Analysis of Two-Dimensional Transistors. IEEE Electron Device Letters, 2021, 42, 94-97.	2.2	2

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37	Bottom-Up Life-Cycle Assessment of MEMS Piezoresistive Pressure Sensors. , 2021, , .		0
38	In-situ recovery of on-membrane PD-SOI MOSFET from TID defects after gamma irradiation. , 2021, , .		0
39	Perovskite Metalâ€“Oxideâ€“Semiconductor Structures for Interface Characterization (Adv. Mater.) Tj ETQq1 1 0.784314 rgBT /Overl	1.9	1
40	Ultra-Thinned Individual SOI Die ACF FC Bonded on Rigid and Flex PCB. , 2021, , .		0
41	Improving MOSFET Piezoresistive Strain Gauges Limit of Detection Using Lock-In Principle. , 2021, , .		0
42	Learning with Physical Noise or Errors. IEEE Transactions on Dependable and Secure Computing, 2020, 17, 957-971.	3.7	3
43	Ultralow Power Ionizing Dose Sensor Based on Complementary Fully Depleted MOS Transistors for Radiotherapy Application. IEEE Transactions on Nuclear Science, 2020, 67, 2217-2223.	1.2	2
44	Impact of hydrogen dopant incorporation on InGaZnO, ZnO and In₂O₃ thin film transistors. Physical Chemistry Chemical Physics, 2020, 22, 1591-1597.	1.3	16
45	Electrodes-oxide-semiconductor device for biosensing: Renewed conformal analysis and multilayer algorithm. Journal of Electroanalytical Chemistry, 2020, 856, 113651.	1.9	3
46	A method for threshold voltage extraction in junctionless MOSFETs using the derivative of transconductance-to-current ratio. Solid-State Electronics, 2020, 168, 107723.	0.8	6
47	A 2.5-GHz Clock Recovery Circuit Based on a Back-Bias-Controlled Oscillator in 28-nm FDSOI. IEEE Solid-State Circuits Letters, 2020, 3, 478-481.	1.3	1
48	Low-Frequency Noise Analysis Of On-Membrane Mosfet And In-Situ Thermal Annealing. , 2020, , .		3
49	New Universal Figure of Merit for Embedded Si Piezoresistive Pressure Sensors. IEEE Sensors Journal, 2020, , 1-1.	2.4	5
50	Optimization of Back Contact Grid Size in Al₂O₃-Rear-Passivated Ultrathin CIGS PV Cells by 2-D Simulations. IEEE Journal of Photovoltaics, 2020, 10, 1908-1917.	1.5	24
51	Enhanced Ultraviolet Avalanche Photodiode With 640-nm-Thin Silicon Body Based on SOI Technology. IEEE Transactions on Electron Devices, 2020, 67, 4641-4644.	1.6	10
52	Black phosphorus field effect transistors stable in harsh conditions via surface engineering. Applied Physics Letters, 2020, 117, .	1.5	7
53	Design Considerations of Ultra-Low-Power Polymer Gas Microsensors Based on Noise Analysis. Proceedings (mdpi), 2020, 56, .	0.2	2
54	Experimental results on diodes and BIMOS ESD devices in 28Ânm FD-SOI under TLP & TID radiation. Microelectronics Reliability, 2020, 114, 113938.	0.9	0

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55	High Voltage Gain WSe₂ Complementary Compact Inverter With Buried Gate for Local Doping. IEEE Electron Device Letters, 2020, 41, 944-947.	2.2	14
56	28-nm FD-SOI CMOS RF Figures of Merit Down to 4.2 K. IEEE Journal of the Electron Devices Society, 2020, 8, 646-654.	1.2	27
57	Self-Heating in FDSOI UTBB MOSFETs at Cryogenic Temperatures and its Effect on Analog Figures of Merit. IEEE Journal of the Electron Devices Society, 2020, 8, 789-796.	1.2	11
58	Structural and Opto-electronic characterization of CuO thin films prepared by DC reactive magnetron sputtering. Journal of Materials Science: Materials in Electronics, 2020, 31, 4563-4573.	1.1	8
59	Performances Evaluation of On-Chip Large-Size-Tapped Transformer for MEMS Applications. IEEE Transactions on Instrumentation and Measurement, 2020, 69, 7051-7060.	2.4	5
60	Electrical characterization of advanced MOSFETs towards analog and RF applications. , 2020, , .		1
61	Schottky-Barrier FET Ultra-Low-Power Diode. , 2020, , .		0
62	Micrometer-thin SOI Sensors for E-Skin Applications. , 2020, , .		1
63	Anisotropic conductive film & flip-chip bonding for low-cost sensor prototyping on rigid & flex PCB. , 2020, , .		1
64	Methodology for Performance Optimization in Noise- and Distortion-Canceling LNA. , 2019, , .		4
65	Low-Power, High-Sensitivity Temperature Sensor Based on Ultrathin SOI Lateral p-i-n Gated Diode. IEEE Transactions on Electron Devices, 2019, 66, 4001-4007.	1.6	3
66	Analysis, Modeling, and Design of a 2.45-GHz RF Energy Harvester for SWIPT IoT Smart Sensors. IEEE Journal of Solid-State Circuits, 2019, 54, 2717-2729.	3.5	41
67	Detection mechanism in highly sensitive ZnO nanowires network gas sensors. Sensors and Actuators B: Chemical, 2019, 297, 126602.	4.0	28
68	A security oriented transient-noise simulation methodology: Evaluation of intrinsic physical noise of cryptographic designs. The Integration VLSI Journal, 2019, 68, 71-79.	1.3	3
69	Light management design in ultra-thin chalcopyrite photovoltaic devices by employing optical modelling. Solar Energy Materials and Solar Cells, 2019, 200, 109933.	3.0	21
70	Defect Selfâ€Compensation for Highâ€Mobility Bilayer InGaZnO/In₂O₃ Thinâ€Film Transistor. Advanced Electronic Materials, 2019, 5, 1900125.	2.6	43
71	Exploring and suppressing the kink effect of black phosphorus field-effect transistors operating in the saturation regime. Nanoscale, 2019, 11, 10420-10428.	2.8	8
72	28-nm FDSOI nMOSFET RF Figures of Merits and Parasitic Elements Extraction at Cryogenic Temperature Down to 77 K. IEEE Journal of the Electron Devices Society, 2019, 7, 810-816.	1.2	12

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73	28â€¯nm FDSOI analog and RF Figures of Merit at N2 cryogenic temperatures. Solid-State Electronics, 2019, 159, 77-82.	0.8	21
74	Enhanced ultraviolet photoresponse in a graphene-gated ultra-thin Si-based photodiode. Journal Physics D: Applied Physics, 2019, 52, 245101.	1.3	10
75	Ultra Low-Loss Si Substrate for On-Chip UWB GHz Antennas. IEEE Journal of the Electron Devices Society, 2019, 7, 393-397.	1.2	7
76	A battery-less BLE smart sensor for room occupancy tracking supplied by 2.45-GHz wireless power transfer. The Integration VLSI Journal, 2019, 67, 8-18.	1.3	17
77	Back-gate bias Effect on the MOSFET-C CMOS UTBB Performance by Circuit Simulations. , 2019, , .		3
78	gm/ID-derivative Method for Threshold Voltage Extraction in Junctionless MOSFETs. , 2019, , .		0
79	Robust Methodology for Low-Frequency Noise Power Analyses in Advanced MOS Transistors. , 2019, , .		4
80	Self-Heating in 28 FDSOI UTBB MOSFETs at Cryogenic Temperatures. , 2019, , .		4
81	Harmonic Distortion in Symmetric and Asymmetric Self-Cascodes of UTBB FD SOI Planar MOSFETs. , 2019, , .		0
82	Subthreshold Operation of Self-Cascode Structure Using UTBB FD SOI Planar MOSFETs. , 2019, , .		1
83	Low-Frequency Noise Transistor Performance for UTBB FDSOI MOSFET-C Filters. , 2019, , .		2
84	Live Demonstration: A Highly Selective Temperature and Humidity Compensated MOX Based Multi-Gas Sensor Module with Bluetooth 5.0 Connectivity. , 2019, , .		0
85	28 FDSOI RF Figures of Merit down to 4.2 K. , 2019, , .		5
86	Surface Passivation of CIGS Solar Cells Using Gallium Oxide. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700826.	0.8	36
87	Analysis and Specification of an IR-UWB Transceiver for High-Speed Chip-to-Chip Communication in a Server Chassis. IEEE Transactions on Circuits and Systems I: Regular Papers, 2018, 65, 2015-2023.	3.5	11
88	Multilevel Half-Rate Phase Detector for Clock and Data Recovery Circuits. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2018, 26, 1807-1811.	2.1	5
89	A Low-Power and In Situ Annealing Technique for the Recovery of Active Devices After Proton Irradiation. EPJ Web of Conferences, 2018, 170, 01006.	0.1	3
90	A Robust 10-Gb/s Duobinary Transceiver in 0.13-Î¼m SOI CMOS for Short-Haul Optical Networks. IEEE Transactions on Industrial Electronics, 2018, 65, 1518-1525.	5.2	2

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91	Development, characterisation and simulation of wafer bonded Si-on-SiC substrates. Materials Science in Semiconductor Processing, 2018, 78, 69-74.	1.9	12
92	Intrinsic rectification in common-gated graphene field-effect transistors. Nano Energy, 2018, 43, 37-46.	8.2	10
93	28 FDSOI RF Figures of Merits and Parasitic Elements at Cryogenic Temperature. , 2018, , .		0
94	8-T ULV SRAM macro in 28nm FDSOI with 7.4 pW/bit retention power and back-biased-scalable speed/energy trade-off. , 2018, , .		5
95	Design of a 2.45-GHz RF Energy Harvester for SWIPT IoT smart sensors. , 2018, , .		4
96	A Transient Noise Analysis of Secured Dual-Rail Based Logic Style. , 2018, , .		0
97	Using Statistical Studentâ€™s t-Test to Qualify the Electrical Performance of the Diamond MOSFETs. , 2018, , .		1
98	Asymmetric Self-Cascode Current-Voltage Constructing Algorithm for Analog Figures-of-Merit Extraction. , 2018, , .		0
99	Numerical Simulation and Analysis of Transistor Channel Length and Doping Mismatching in GC SOI nMOSFETs Analog Figures of Merit. , 2018, , .		0
100	Linearity Enhancement in Asymmetric Self-Cascode Composed by FD SOI nMOSFETs. , 2018, , .		0
101	A Battery-Less BLE IoT Motion Detector Supplied by 2.45-GHz Wireless Power Transfer. , 2018, , .		9
102	Fully-Depleted SOI MOSFET Sensors in Accumulation Mode for Total Dose Measurement. , 2018, , .		2
103	28 FDSOI analog and RF Figures of Merit at cryogenic temperatures. , 2018, , .		7
104	Low-power half-rate dual-loop clock-recovery system in 28-nm FDSOI. , 2018, , .		3
105	Understanding hydrogen and nitrogen doping on active defects in amorphous In-Ga-Zn-O thin film transistors. Applied Physics Letters, 2018, 112, .	1.5	28
106	Waferâ€Scale Nanoimprint Lithography Process Towards Complementary Silicon Nanowire Fieldâ€Effect Transistors for Biosensor Applications. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1800234.	0.8	10
107	Gradient importance sampling: An efficient statistical extraction methodology of high-sigma SRAM dynamic characteristics. , 2018, , .		16
108	Design benefits of self-cascode configuration for analog applications in 28 FDSOI. , 2018, , .		1

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109	Quantum Efficiency Improvement of SOI p-i-n Lateral Diodes Operating as UV Detectors at High Temperatures. IEEE Sensors Journal, 2017, 17, 1641-1648.	2.4	5
110	Boosting the SOI MOSFET Electrical Performance by Using the Octagonal Layout Style in High Temperature Environment. IEEE Transactions on Device and Materials Reliability, 2017, 17, 221-228.	1.5	6
111	Multiple-Wavelength Detection in SOI Lateral PIN Diodes With Backside Reflectors. IEEE Transactions on Industrial Electronics, 2017, 64, 7368-7376.	5.2	6
112	A Quasi-Static Model of Silicon Substrate Effects in Graphene Field Effect Transistors. IEEE Electron Device Letters, 2017, 38, 987-990.	2.2	5
113	In-situthermal annealing of on-membrane silicon-on-insulator semiconductor-based devices after high gamma dose irradiation. Nanotechnology, 2017, 28, 184001.	1.3	9
114	Optimisation of rear reflectance in ultra-thin CIGS solar cells towards >20% efficiency. Solar Energy, 2017, 146, 443-452.	2.9	38
115	Reliable characteristics and stabilization of on-membrane SOI MOSFET-based components heated up to 335 Â°C. Semiconductor Science and Technology, 2017, 32, 014001.	1.0	9
116	Leakage Current and Low-Frequency Noise Analysis and Reduction in a Suspended SOI Lateral p-i-n Diode. IEEE Transactions on Electron Devices, 2017, 64, 4252-4259.	1.6	8
117	Design and Fabrication of Silicon-on-Silicon-Carbide Substrates and Power Devices for Space Applications. E3S Web of Conferences, 2017, 16, 12003.	0.2	1
118	Addressing the impact of rear surface passivation mechanisms on ultra-thin Cu(In,Ga)Se2 solar cell performances using SCAPS 1-D model. Solar Energy, 2017, 157, 603-613.	2.9	45
119	Scaling Trends for Dual-Rail Logic Styles Against Side-Channel Attacks: A Case-Study. Lecture Notes in Computer Science, 2017, , 19-33.	1.0	8
120	Comparative study of non-linearities in 28 nm node FDSOI and Bulk MOSFETs. , 2017, , .		9
121	Back-gate bias effect on FDSOI MOSFET RF Figures of Merits and parasitic elements. , 2017, , .		9
122	Automated layout-integrated sizing of a 2.45 GHz differential-drive rectifier in 28 nm FDSOI CMOS. , 2017, , .		0
123	RF SOI CMOS technology on 1st and 2nd generation trap-rich high resistivity SOI wafers. Solid-State Electronics, 2017, 128, 121-128.	0.8	13
124	An in-depth analysis of temperature effect on DIBL in UTBB FD SOI MOSFETs based on experimental data, numerical simulations and analytical models. Solid-State Electronics, 2017, 128, 67-71.	0.8	2
125	An 80-MHz 0.4V ULV SRAM macro in 28nm FDSOI achieving 28-fJ/bit access energy with a ULP bitcell and on-chip adaptive back bias generation. , 2017, , .		9
126	High-efficiency wireless power transfer for mm-size biomedical implants. , 2017, , .		5

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127	Improving noise and linearity of CMOS wideband inductorless balun LNAs for 10-GHz software-defined radios in 28nm FDSOI. , 2017, , .		2
128	Back-gate bias effect on UTBB-FDSOI non-linearity performance. , 2017, , .		5
129	Single event effects and total ionising dose in 600V Si-on-SiC LDMOS transistors for rad-hard space applications. , 2017, , .		5
130	Channel width influence on the analog performance of the asymmetric self-cascode FD SOI nMOSFETs. , 2017, , .		1
131	Experimental evaluation of mismatching on the analog characteristics of GC SOI MOSFETs. , 2017, , .		1
132	Comparative experimental study of the improved MOSFETs matching by using the hexagonal layout style. , 2017, , .		1
133	Effect of the back bias on the analog performance of standard FD and UTBB transistors-based self-cascode structures. Semiconductor Science and Technology, 2017, 32, 095005.	1.0	2
134	Artificial Microsystems for Sensing Airflow, Temperature, and Humidity by Combining MEMS and CMOS Technologies. , 2017, , 243-256.		0
135	Origin of the Low-Frequency Noise in the Asymmetric Self-Cascode Structure Composed by Fully Depleted SOI nMOSFETs. Journal of Integrated Circuits and Systems, 2017, 12, 62-70.	0.3	1
136	Experimental and simulation analysis of electrical characteristics of commonâ€source current mirrors implemented with asymmetric selfâ€cascode siliconâ€onâ€insulator nâ€channel metalâ€“oxideâ€“semiconductor fieldâ€effect transistors. IET Circuits, Devices and Systems, 2016, 10, 349-355.	0.9	2
137	Boosting the MOSFETs matching by using diamond layout style. , 2016, , .		4
138	Efficient passive energy harvesters at 950 MHz and 2.45 GHz for 100 Î¼W applications in 65 nm CMOS. , 2016, , .		1
139	Low power highly linear temperature sensor based on SOI lateral PIN diodes. , 2016, , .		4
140	Use of back gate bias to improve the performance of n- and p-type UTBB transistors-based self-cascode structures applied to current mirrors. , 2016, , .		3
141	Operation of suspended lateral SOI PIN photodiode with aluminum back gate. , 2016, , .		5
142	Analysis and modelling of temperature effect on DIBL in UTBB FD SOI MOSFETs. , 2016, , .		3
143	Automated Design of a 13.56 MHz 19 ÂµW Passive Rectifier With 72% Efficiency Under 10 ÂµA load. IEEE Journal of Solid-State Circuits, 2016, 51, 1290-1301.	3.5	22
144	Electronic properties of negatively charged SiOx films deposited by Atmospheric Pressure Plasma Liquid Deposition for surface passivation of p-type c-Si solar cells. Thin Solid Films, 2016, 611, 74-77.	0.8	1

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145	CAMEL. , 2016, , .		0
146	Role of Ionic Strength in Staphylococcal Cell Aggregation. Langmuir, 2016, 32, 7277-7283.	1.6	11
147	Low-frequency noise in asymmetric self-cascode FD SOI nMOSFETs. , 2016, , .		0
148	Improved operation of graded-channel SOI nMOSFETs down to liquid helium temperature. Semiconductor Science and Technology, 2016, 31, 114005.	1.0	4
149	Junctionless nanowire transistors operation at temperatures down to 4.2 K. Semiconductor Science and Technology, 2016, 31, 114001.	1.0	17
150	Automated design of a 13.56 MHz corner-robust efficient differential drive rectifier for 10 Î¼A load. , 2016, , .		3
151	A hybrid graphene-metal oxide sensor for formaldehyde detection at room temperature. , 2016, , .		0
152	Low-frequency noise of submicron graded-channel SOI nMOSFETs at high temperature. , 2016, , .		0
153	Assessment of 28 nm UTBB FD-SOI technology platform for RF applications: Figures of merit and effect of parasitic elements. Solid-State Electronics, 2016, 117, 130-137.	0.8	45
154	On the improvement of DC analog characteristics of FD SOI transistors by using asymmetric self-cascode configuration. Solid-State Electronics, 2016, 117, 152-160.	0.8	18
155	RF SOI CMOS technology on 1st and 2nd generation trap-rich high resistivity SOI wafers. , 2016, , .		1
156	A review of special gate coupling effects in long-channel SOI MOSFETs with lightly doped ultra-thin bodies and their compact analytical modeling. Solid-State Electronics, 2016, 117, 66-76.	0.8	14
157	Silicon-on-Insulator Photodiode on Micro-Hotplate Platform With Improved Responsivity and High-Temperature Application. IEEE Sensors Journal, 2016, 16, 3017-3024.	2.4	13
158	Quantitative characterization of biofunctionalization layers by robust image analysis for biosensor applications. Sensors and Actuators B: Chemical, 2016, 222, 980-986.	4.0	4
159	Capacitive Biosensing of Bacterial Cells: Sensitivity Optimization. IEEE Sensors Journal, 2016, 16, 586-595.	2.4	10
160	Comparison of self-heating and its effect on analogue performance in 28 nm bulk and FDSOI. Solid-State Electronics, 2016, 115, 219-224.	0.8	21
161	A 16 x 16 CMOS Capacitive Biosensor Array Towards Detection of Single Bacterial Cell. IEEE Transactions on Biomedical Circuits and Systems, 2016, 10, 364-374.	2.7	61
162	Towards Securing Low-Power Digital Circuits with Ultra-Low-Voltage Vdd Randomizers. Lecture Notes in Computer Science, 2016, , 233-248.	1.0	4

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163	Investigating the electronic properties of Al2O3/Cu(In,Ga)Se2 interface. AIP Advances, 2015, 5, .	0.6	69
164	A low-power and in situ annealing mitigation technique for fast neutrons irradiation of integrated temperature sensing diodes. , 2015, , .		3
165	Highly reflective rear surface passivation design for ultra-thin Cu(In,Ga)Se 2 solar cells. Thin Solid Films, 2015, 582, 300-303.	0.8	51
166	Study of Total Quantum Efficiency of Lateral SOI PIN Photodiodes with Back-Gate Bias, Intrinsic Length and Temperature Variation. ECS Transactions, 2015, 66, 101-107.	0.3	2
167	Resonant dielectrophoresis and electrohydrodynamics for high-sensitivity impedance detection of whole-cell bacteria. Lab on A Chip, 2015, 15, 3183-3191.	3.1	17
168	Trigate nanowire MOSFETs analog figures of merit. Solid-State Electronics, 2015, 112, 78-84.	0.8	15
169	Analog performance improvement of self-cascode structures composed by UTBB transistors using back gate bias. , 2015, , .		6
170	Advantages of subthreshold operation of asymmetric self-cascode SOI transistors aiming at analog circuit applications. , 2015, , .		2
171	Boosting the total ionizing dose tolerance of digital switches by using OCTO SOI MOSFET. Semiconductor Science and Technology, 2015, 30, 105024.	1.0	11
172	A 0.48mm² 5μW-10mW indoor/outdoor PV energy-harvesting management unit in a 65nm SoC based on a single bidirectional multi-gain/multi-mode switched-cap converter with supercap storage. , 2015, , .		6
173	Comparative study of parasitic elements on RF FoM in 28 nm FD SOI and bulk technologies. , 2015, , .		8
174	Can we connect trillions of IoT sensors in a sustainable way? A technology/circuit perspective (Invited). , 2015, , .		30
175	Use of back gate bias to enhance the analog performance of planar FD and UTBB SOI transistors-based self-cascode structures. , 2015, , .		3
176	Wide band study of silicon-on-insulator photodiodes on suspended micro-hotplates platforms. , 2015, , .		5
177	Towards ultra-low-voltage wideband noise-cancelling LNAs in 28nm FDSOI. , 2015, , .		6
178	A Capacitance-to-Frequency Converter With On-Chip Passivated Microelectrodes for Bacteria Detection in Saline Buffers Up to 575 MHz. IEEE Transactions on Circuits and Systems II: Express Briefs, 2015, 62, 159-163.	2.2	32
179	Capacitive biosensing of bacterial cells: Analytical model and numerical simulations. Sensors and Actuators B: Chemical, 2015, 211, 428-438.	4.0	32
180	Influence of Ga/(Ga + In) grading on deepâ€defect states of Cu(In,Ga)Se₂ solar cells. Physica Status Solidi - Rapid Research Letters, 2015, 9, 157-160.	1.2	14

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181	Wide frequency band assessment of 28nm FDSOI technology platform for analogue and RF applications. Solid-State Electronics, 2015, 108, 47-52.	0.8	29
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